

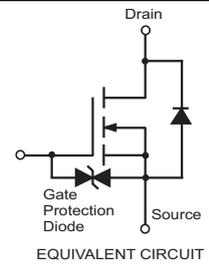
**FEATURE**

- High density cell design for low  $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD Protected Up To 2kV

**MAXIMUM RATINGS ( $T_a=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	20	V
Continuous Drain Current	$I_D$	0.3	A
Power Dissipation	$P_D$	0.225	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	556	$^{\circ}C/W$
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-50 ~+150	

**2N7002K**  
N-Channel MOSFET



$T_a=25^{\circ}C$  unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate-Threshold Voltage	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	2.5	
Gate-body Leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 80$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$			80	nA
On-state Drain Current	$I_{D(ON)}$	$V_{GS}=10V, V_{DS}=7V$	500			mA
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=500mA$		0.9	5	$\Omega$
		$V_{GS}=5V, I_D=50mA$		1.1	7	
Forward Trans conductance	$g_{fs}$	$V_{DS}=10V, I_D=200mA$	80			ms
Drain-source on-voltage	$V_{DS(on)}$	$V_{GS}=10V, I_D=500mA$			3.75	V
		$V_{GS}=5V, I_D=50mA$			0.375	V
Diode Forward Voltage	$V_{SD}$	$I_S=115mA, V_{GS}=0V$	0.55		1.2	V
Input Capacitance *	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1MHz$			50	pF
Output Capacitance *	$C_{oss}$				25	
Reverse Transfer Capacitance *	$C_{rss}$				5	

**SWITCHING TIME**

Turn-on Time *	$t_{d(on)}$	$V_{DD}=25V, R_L=50\Omega,$ $I_D=500mA, V_{GEN}=10V$			20	ns
Turn-off Time *	$t_{d(off)}$	$R_G=25\Omega$			40	

\*These parameters have no way to verify.

**2N7002K**

